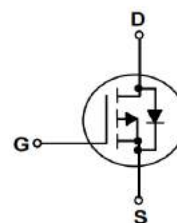
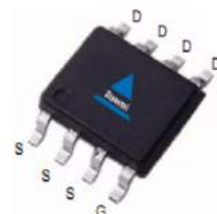


Features

- P-Channel
- Very low on-resistance $R_{DS(on)}$
- Reliable and Rugged
- Avalanche Rated
- 100% EAS Tested

| | | |
|--------------------------------|-----|------------|
| V_{DS} | -30 | V |
| $R_{DS(on),TYP@ V_{GS}=-10V}$ | 8 | m Ω |
| $R_{DS(on),TYP@ V_{GS}=-4.5V}$ | 12 | m Ω |
| I_D | -12 | A |

SOP-8


| Part ID | Package Type | Marking | Packing |
|-----------|--------------|-----------|--------------|
| ZT090P03S | SOP-8 | ZT090P03S | 4000pcs/reel |

Absolute Maximum Ratings $T_A = 25^\circ\text{C}$, unless otherwise specified

| Symbol | Parameter | Rating | Unit | |
|--|---|---------------------------------|--------------------|---|
| Common Ratings ($T_C=25^\circ\text{C}$ Unless Otherwise Noted) | | | | |
| V_{GS} | Gate-Source Voltage | ± 25 | V | |
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | -30 | V | |
| T_J | Maximum Junction Temperature | 150 | $^\circ\text{C}$ | |
| T_{STG} | Storage Temperature Range | -55 to 150 | $^\circ\text{C}$ | |
| I_{DM} | Drain Current-Continuous@ Current-Pulsed (Note 1) | $T_C = 25^\circ\text{C}$ -54 | A | |
| Mounted on Large Heat Sink | | | | |
| I_D | Drain Current-Continuous | $T_C = 25^\circ\text{C}$ | -12 | A |
| | | $T_C = 100^\circ\text{C}$ | -8 | A |
| P_D | Maximum Power Dissipation | $T_C = 25^\circ\text{C}$ | 3.6 | W |
| | | $T_C = 100^\circ\text{C}$ | 1.4 | W |
| $R_{\theta JC}$ | Thermal Resistance-Junction to Case | 35.7 | $^\circ\text{C/W}$ | |
| Drain-Source Avalanche Ratings | | | | |
| EAS | Avalanche Energy, Single Pulsed (Note 2) | 225 | mJ | |

Electrical Characteristics (T_J=25°C unless otherwise noted)

| Symbol | Parameter | Condition | Min | Typ | Max | Unit |
|---|--|---|------|------|------|------|
| Static Electrical Characteristics @ T_J=25°C (unless otherwise stated) | | | | | | |
| V(BR)DSS | Drain-Source Breakdown Voltage | V _{GS} =0V, I _D =-250μA | -30 | -- | -- | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =-30V, V _{GS} =0V | -- | -- | -1 | μA |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} =±25V, V _{DS} =0V | -- | -- | ±100 | nA |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =-250μA | -1.0 | -1.5 | -2.0 | V |
| R _{DS(on)} | Drain-Source On-State Resistance | V _{GS} =-10V, I _D =-12A | -- | 8 | 10.5 | mΩ |
| R _{DS(on)} | Drain-Source On-State Resistance | V _{GS} =-4.5V, I _D =-7A | -- | 12 | 16 | mΩ |
| g _{FS} | Forward Transconductance | V _{DS} =-5V, I _D =-20A | -- | 60 | -- | S |
| Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated) | | | | | | |
| C _{iss} | Input Capacitance | V _{DS} =-15V, V _{GS} =0V, f=1MHz | -- | 1780 | -- | pF |
| C _{oss} | Output Capacitance | | -- | 240 | -- | pF |
| C _{rss} | Reverse Transfer Capacitance | | -- | 205 | -- | pF |
| R _g | Gate Resistance | f=1MHz | -- | 2.5 | -- | Ω |
| Q _g | Total Gate Charge | V _{DS} =-15V, I _D =-15A, V _{GS} =-10V | -- | 46 | -- | nC |
| Q _{gs} | Gate-Source Charge | | -- | 1.0 | -- | nC |
| Q _{gd} | Gate-Drain Charge | | -- | 1.4 | -- | nC |
| Switching Characteristics | | | | | | |
| T _{d(on)} | Turn-on Delay Time | V _{DS} =-15V, R _L =1Ω, R _G =3Ω, V _{GS} =-10V | -- | 8 | -- | ns |
| T _r | Turn-on Rise Time | | -- | 27 | -- | ns |
| T _{d(off)} | Turn-Off Delay Time | | -- | 68 | -- | ns |
| T _f | Turn-Off Fall Time | | -- | 39 | -- | ns |
| Source- Drain Diode Characteristics @ T_J = 25°C (unless otherwise stated) | | | | | | |
| I _{SD} | Source-Drain Current (Body Diode) | | -- | -- | -12 | A |
| V _{SD} | Forward on voltage ^(Note 3) | I _S =-20A, V _{GS} =0V | -- | -- | 1.2 | V |
| T _{rr} | Reverse Recovery Time | T _J =25°C, I _{SD} =-4A, V _{GS} =0V | -- | 13.5 | -- | ns |
| Q _{rr} | Reverse Recovery Charge | di/dt=100A/μs | -- | 3.7 | -- | nC |

Notes :

- 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2.E_{AS} condition: T_J=25°C, V_{DS}=-30V, V_{GS}=-10V, R_G=25Ω, L=0.5mH.
- 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)

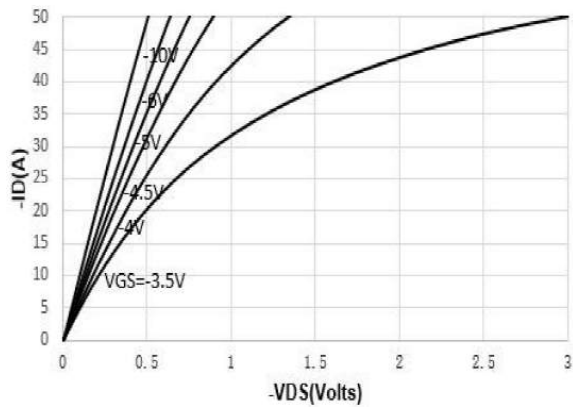


Figure 1. On-Regin Characteristics

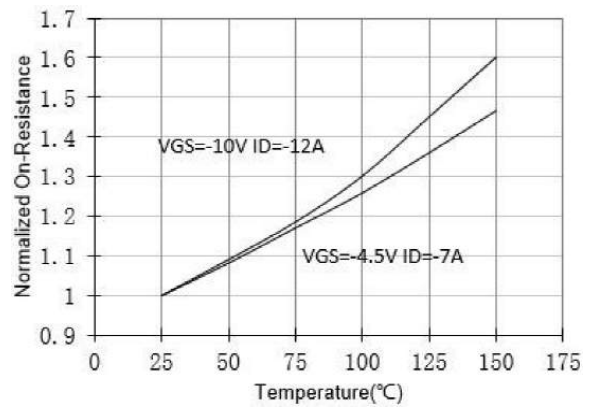


Figure 4. On-Resistance vs. Junction Temperature

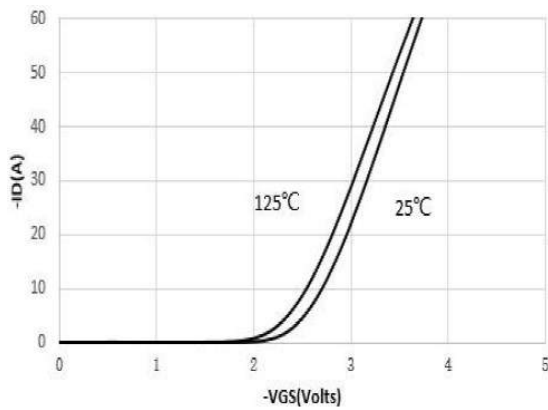


Figure 2. Transfer Characteristics

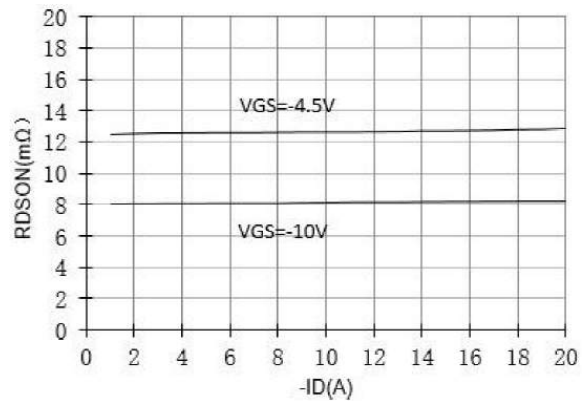


Figure 5. On-Resistance vs. Drain Current and Gate Voltage

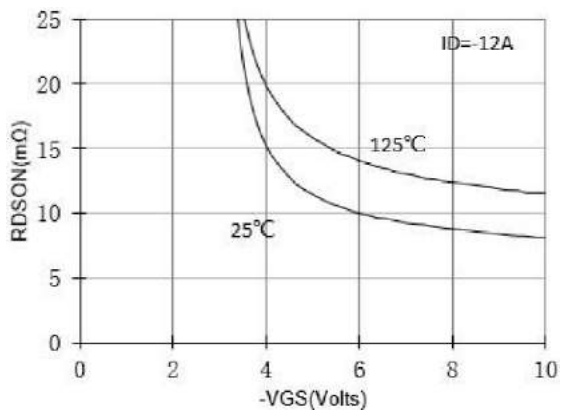


Figure 3. On-Resistance vs. Gate-Source Voltage

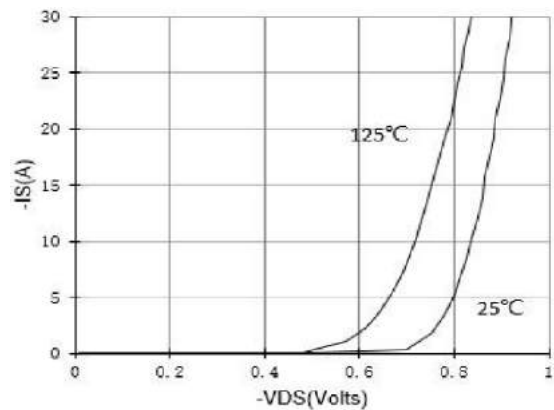


Figure 6. Body-Diode Characteristics

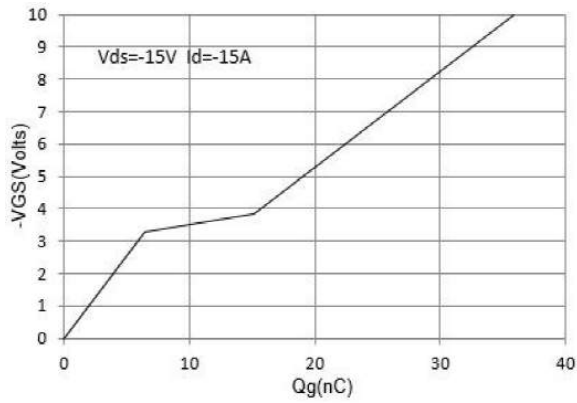


Figure 7 Gate-Charge Characteristics

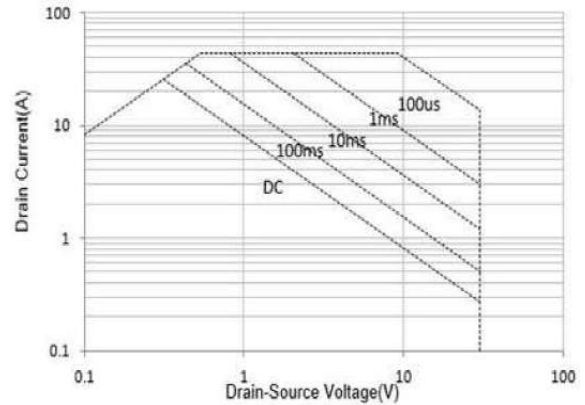


Figure 9. Maximum Forward Biased Safe Operating Area

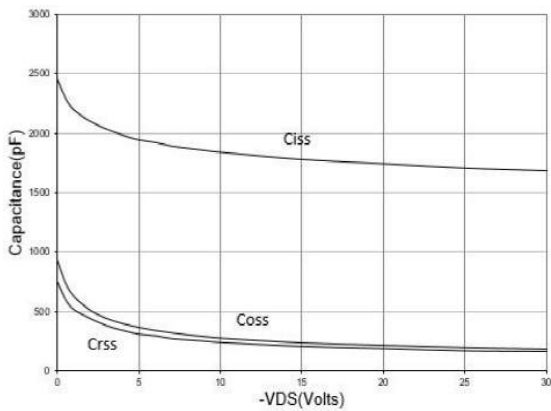


Figure 8 Capacitance Characteristics

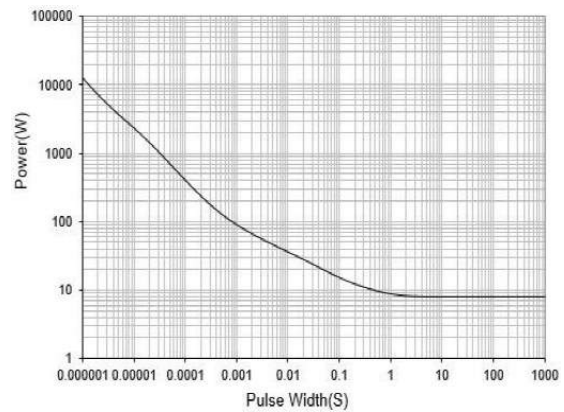


Figure 10. Single Pulse Power Rating Junction-to-Ambient

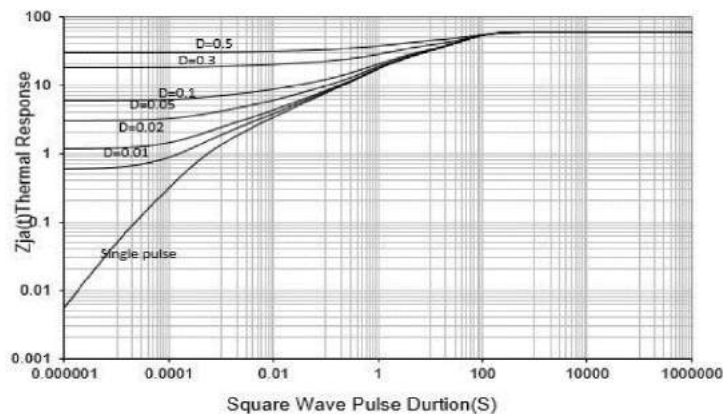
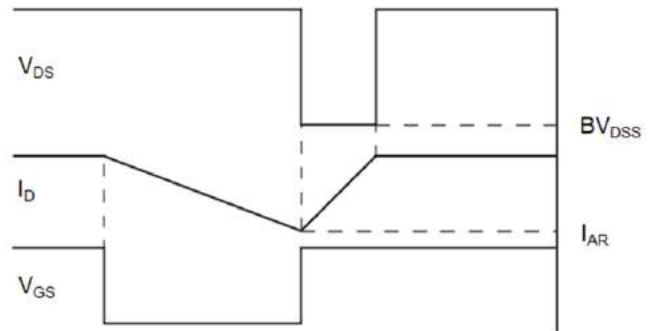
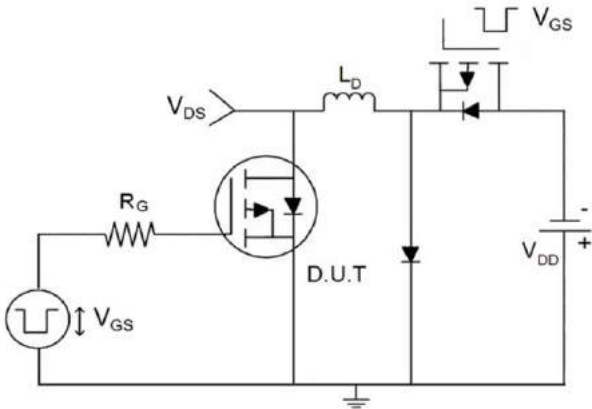


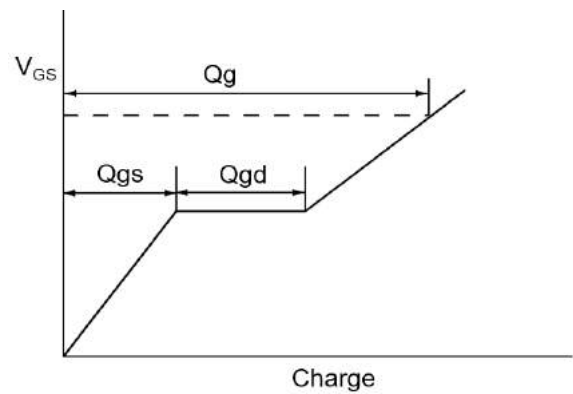
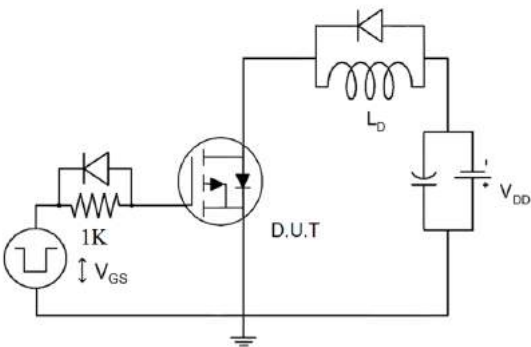
Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

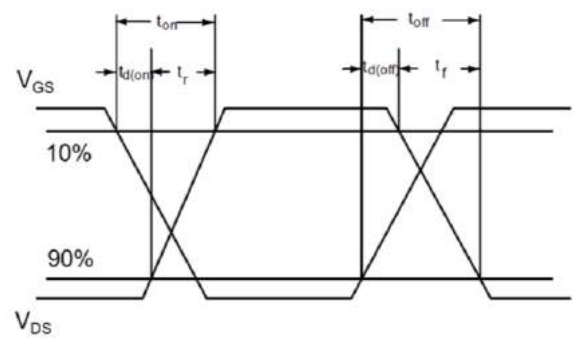
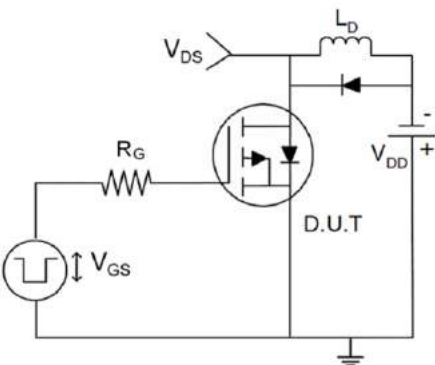
1) E_{AS} Test Circuits



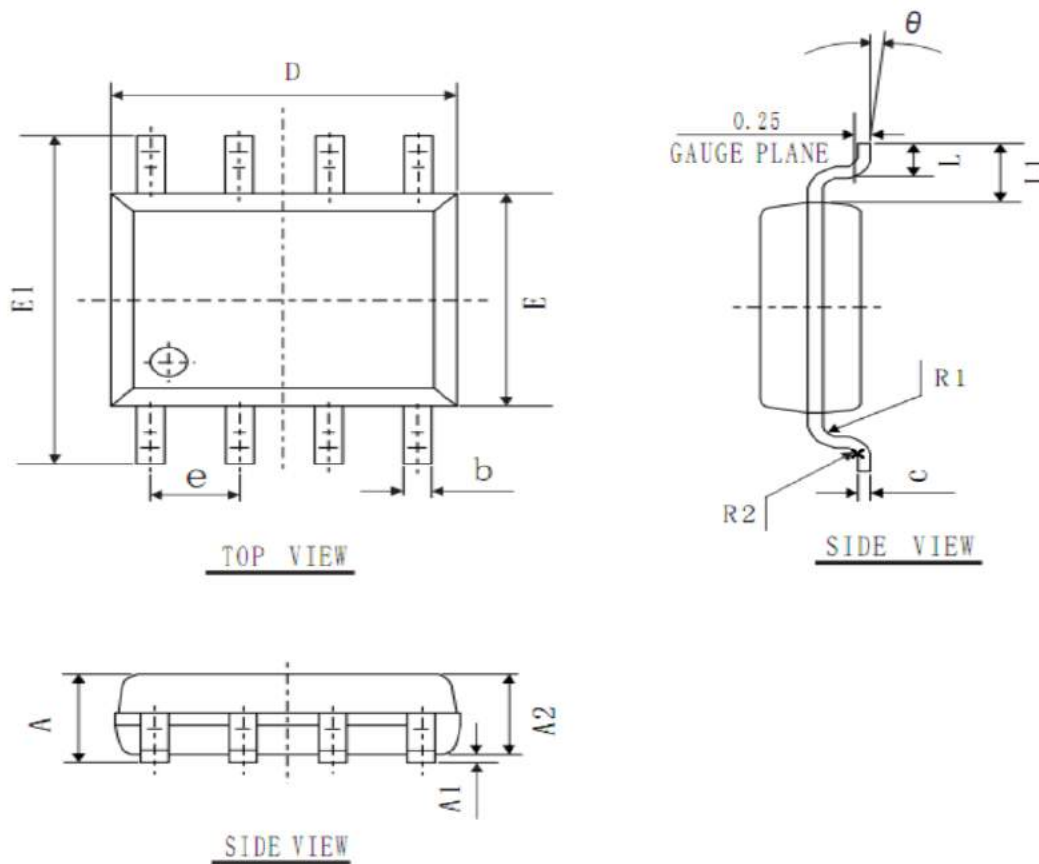
2) Gate Charge Test Circuit



3) Switch Time Test Circuit



SOP-8 Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

| SYMBOL | MIN | NOM | MAX |
|----------|----------|-------|-------|
| A | 1.40 | 1.60 | 1.80 |
| A1 | 0.05 | 0.15 | 0.25 |
| A2 | 1.35 | 1.45 | 1.55 |
| b | 0.30 | 0.40 | 0.50 |
| c | 0.153 | 0.203 | 0.253 |
| D | 4.80 | 4.90 | 5.00 |
| E | 3.80 | 3.90 | 4.00 |
| E1 | 5.80 | 6.00 | 6.20 |
| L | 0.45 | 0.70 | 1.00 |
| θ | 2° | 4° | 6° |
| L1 | 1.04 REF | | |
| e | 1.27 BSC | | |
| R1 | 0.07 TYP | | |
| R2 | 0.07 TYP | | |

Customer Service

Sales and Service:

zj@ztasemi.com